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Information for form 1449A/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)

Completion of Required

Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Geusic, Joseph
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet **152**

Attorney Docket No: 303.390US4

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EXAMINER

Julius J. Haldorson

DATE CONSIDERED

01/25/2005

Substantive Examination Statement Form (PTO-1449)
 * EXAMINER: select a reference construction, whether or not election is in contemplation with AIA/PTO 2003. Other the design election if not in contemplation and not considered. Include copy of this form with each communication to applicant. Applicant's unique citation designation number (optional) Applicant is to provide a check mark item if English language translation is checked

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Substituted for form 1449A-P10 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if known <table border="1"> <tr> <td>Application Number</td> <td>Unknown</td> </tr> <tr> <td>Filing Date</td> <td>Even Date Herewith</td> </tr> <tr> <td>First Named Inventor</td> <td>Geusic, Joseph</td> </tr> <tr> <td>Group Art Unit</td> <td>Unknown</td> </tr> <tr> <td>Examiner Name</td> <td>Unknown</td> </tr> </table>		Application Number	Unknown	Filing Date	Even Date Herewith	First Named Inventor	Geusic, Joseph	Group Art Unit	Unknown	Examiner Name	Unknown
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First Named Inventor	Geusic, Joseph												
Group Art Unit	Unknown												
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EXAMINER

Julius H. Haddad

DATE CONSIDERED

06/20/05

Substitution Statement: Substitution Form (PTO-1443)
* EXAMINER: Initials of inventor, check for and citation in the examination file (MPEP 2003, 2004) and for citation in the examination file and examination. Initials may of this form can not contribute to the examination. Applicant's written statement (signature) must be included in the file to place a check mark here if English language translation is correct.